TO-92 Plastic-Encapsulate Transistors

BC308 TRANSISTOR（ NPN ）

FEATURES

Power dissipation

P_{CM}: 0.350 W（Tamb=25℃）

Collector current

I_{CM}: 0.5 A

Collector-base voltage

$V_{(BR)CBO}$: 30 V

Operating and storage junction temperature range

T_J，T_{stg}: -55℃ to +150℃

TO—92

ELECTRICAL CHARACTERISTICS（Tamb=25℃ unless otherwise specified）

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	I_C=10μA， I_E=0	-30			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	I_C=20mA， I_B=0	-25			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E=10μA， I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-25 V， I_E=0			-15	μA
Emitter cut-off current	I_{EBO}	V_{EB}= 5 V， I_C=0			-15	μA
DC current gain(note)	V_{CE}(sat)	V_{CE}=10V, I_C=2mA	120		800	
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=10mA, I_B=0.5mA			-0.3	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C=10mA, I_B=0.5mA			-0.75	V
Base-emitter voltage	V_{BE}	V_{CE}=5V, I_C=2mA	-0.55		-0.75	V
Transition frequency	f_T	V_{CE}=5V, I_C=10mA f=50MHz		130		MHz

CLASSIFICATION

HFE

Rank	1	2	3
Range	100-300	300-500	500-800